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(2/00)

AMENDED CLAIMS					
	NO. OF CLAIMS	HIGHEST NO. OF CLAIMS PREVIOUSLY PAID FOR	EXTRA CLAIMS	RATE	ADDT'L FEE
Total Claims		MINUS =		× \$18.00 (103) =	
Independent Claims		MINUS =		× \$78.00 (102) =	
If Amendment adds multiple dependent claims, add \$260.00 (104)					
Total Amendment Fee					
If small entity status is claimed, subtract 50% of Total Amendment Fee					
TOTAL ADDITIONAL FEE DUE FOR THIS AMENDMENT					


☐ A claim fee in the amount of \$_____ is enclosed.

☐ Charge \$_____ to Deposit Account No. 02-4800.

The Commissioner is hereby authorized to charge any appropriate fees under 37 C.F.R. §§ 1.16, 1.17, 1.20(d) and 1.21 that may be required by this paper, and to credit any overpayment, to Deposit Account No.02-4800. This paper is submitted in duplicate.

Respectfully submitted,

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Date: May 4, 2000

Patent

Attorney's Docket No. 032840-003

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

Ted JOHANSSON et al.

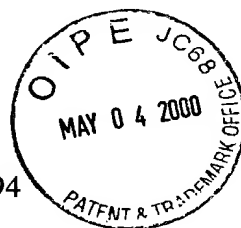
Application No.: 09/500,994

Filed: February 9, 2000

For: SEMICONDUCTOR DEVICE WITH
DEEP SUBSTRATE CONTACTS

Group Art Unit: 2811

Examiner: Unassigned



PRELIMINARY AMENDMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

Prior to initial examination, please amend the above-identified patent application as follows.

IN THE CLAIMS

~~Please cancel claim 10 without prejudice or disclaimer.~~

Please add new claim 11 as follows:

--11. A semiconductor integrated circuit mounted in a package, said package having a plurality of pins connecting to the semiconductor circuit, and said circuit having a plurality of semiconductor devices, wherein at least one of said semiconductor devices is a semiconductor device arranged at a surface of a semiconductor substrate, having an initial doping, said device having an electrical connection comprising at least one plug made of a material with a high conductivity, between said initially doped substrate and said surface of